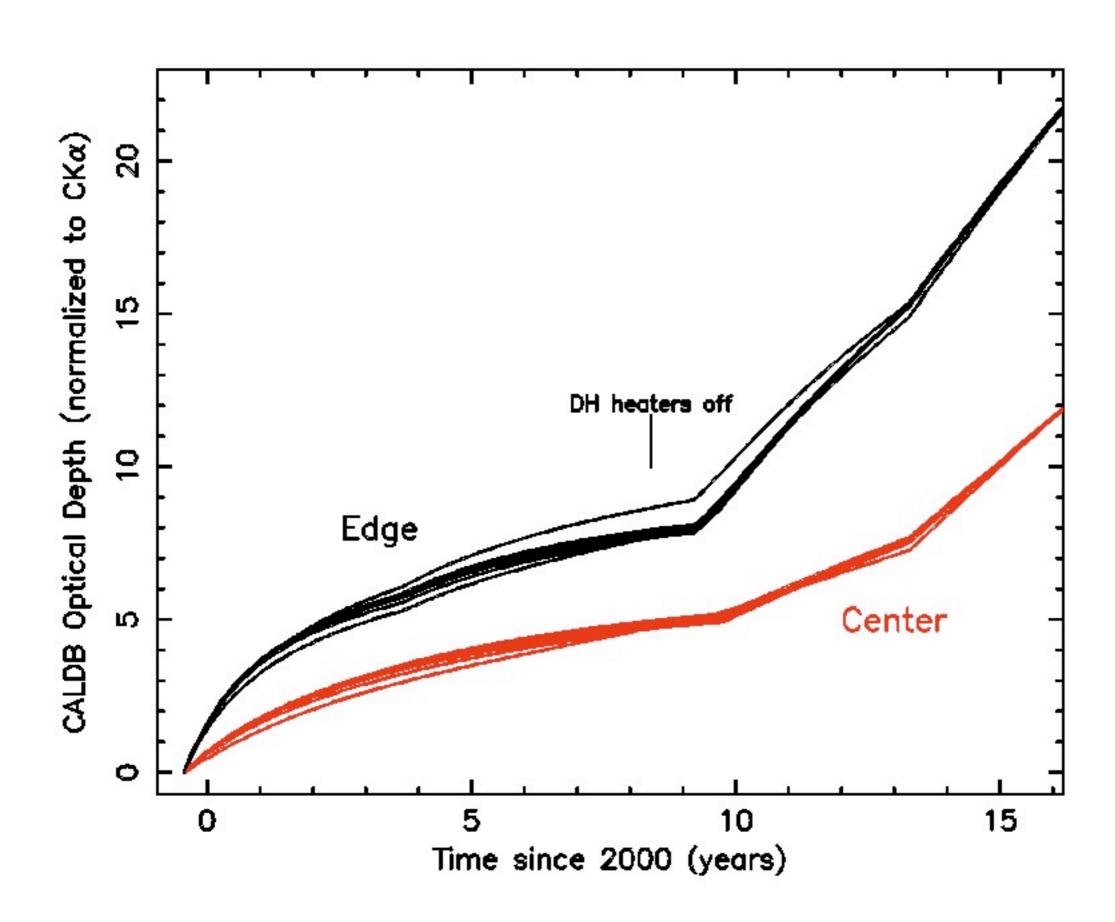
Doug Swartz & Steve O'Dell

Motivation:

The accelerated accumulation observed since ~2012 cannot be reproduced under the old assumptions of one (or more) gradually depleting contaminant source(s) -- any new paradigm must consider source(s) with rates *increasing* with time (but consistent within S/C trends).

Methods: (the usual)

- (1) Simulate migration (vaporization/deposition) of potential contaminant(s) by solving a set of 1st order ODEs through explicit (forward) difference scheme and within thermal & geometric model constraints.
- (2) Compare time evolution of material mass column density to observations at select locations on OBF filters to identify best candidate contaminant properties.



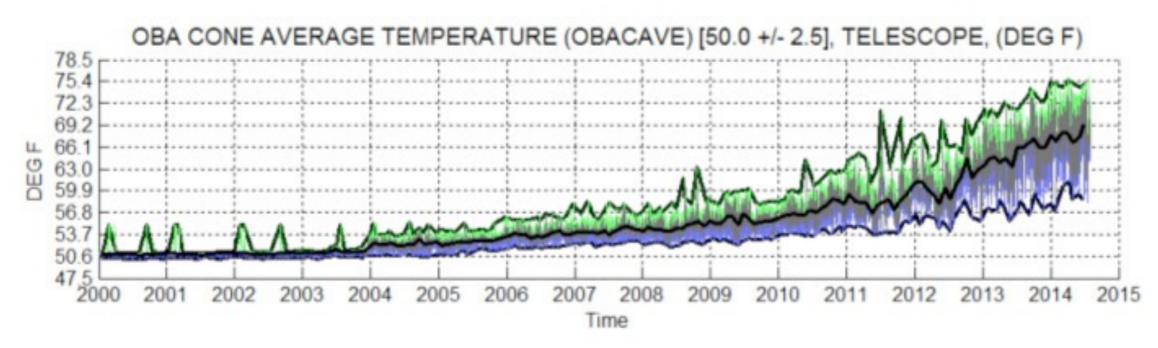
Simulation Constraints:

- ◆ Spacecraft geometry (surface areas & view factors) and time-averaged surface temperatures as determined by Neil Tice (LM) using flight data inputs to Thermal DesktopTM RADCAD (geometric) & SINDA FLUINT (radiative/conductive thermal) modules; accounts for effects of DH heaters being turned off ~2008.4 (t~9 yr)
- X-ray observations of contamination effects throughout the mission as documented in CALDB contamination model N0009 (June 2014); constrains time evolution and spatial distribution of contaminant optical depth, $\tau(t,x,y)$, proportional to the mass surface density, $\mu(t,x,y)$
- ◆ Temperature dependence of vaporization rate follows Clausius-Clapeyron relation $\rho(T) = \rho(T_0) \ (T/T_0)^{1/2} exp(-\Delta H(1/T-1/T_0)/R)$ where $\rho(T)$ is the mass vaporization rate at temperature T, ΔH is the vaporization enthalpy, and R the universal gas constant

Simulation Parameters:

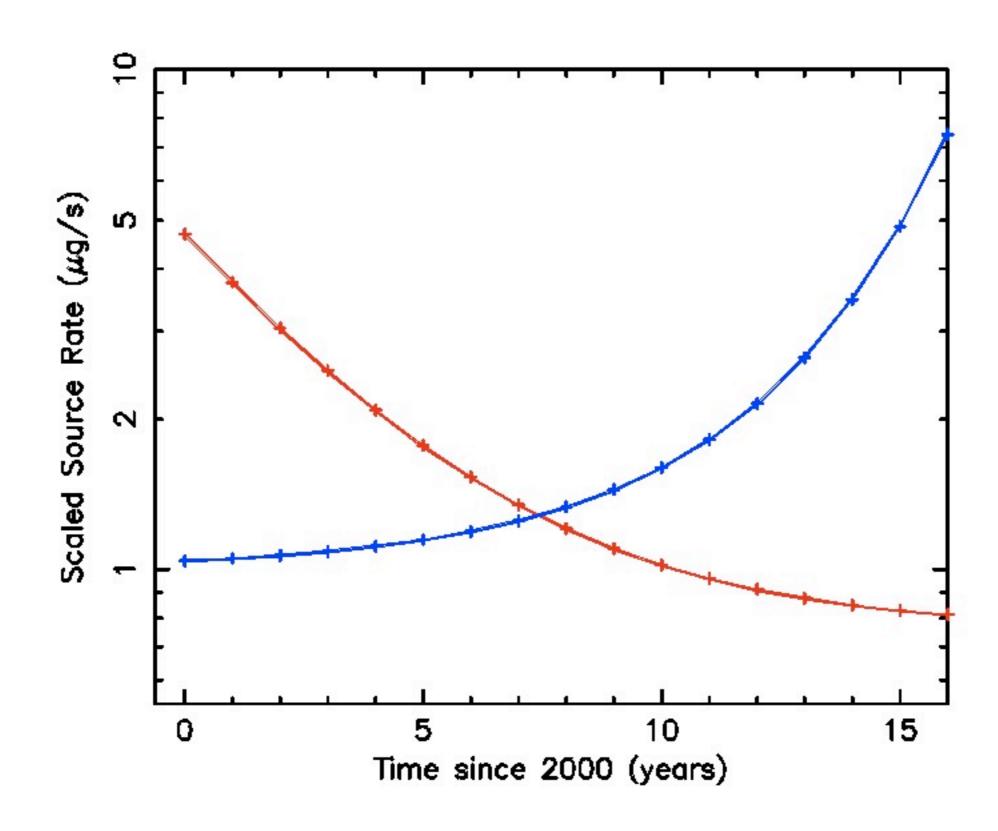
- ♦ Material (enthalpy, ΔH , and reference temperature, T_0 , fixed); vaporization rate normalization $\rho(T_0)$ is a free parameter
- ♦ Declining source rate: S(t)=A(1+B*exp(-t/C)) where A, B & C are chosen to follow the early build-up (t<2008) at the center of S3
- ♦ Rising source rate: $S'(t) \propto A' \exp(-B'(1/T-1/T_0))$ where the normalization, A' is a free parameter and B' is given by the enthalpy ΔH of the supposed contaminant. Physically, A' includes a multiplicative scale factor representing the outgassing 'escape efficiency'.

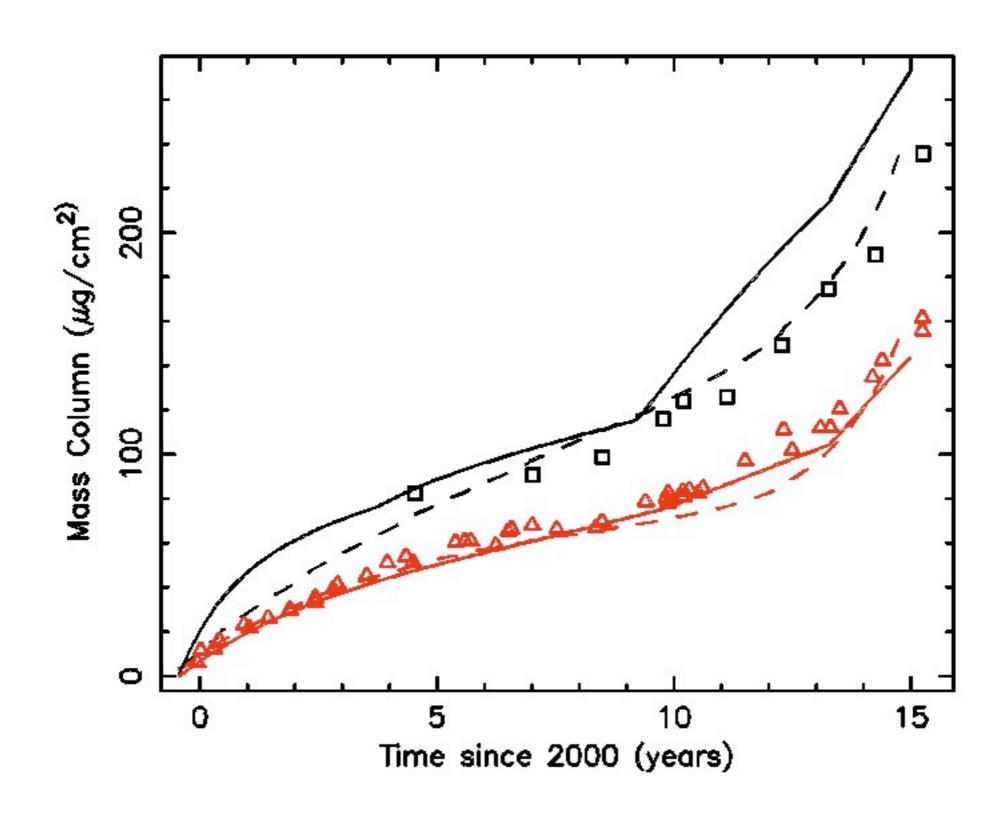
$$T_{\text{OBA}}(t) = T_0 [1+0.006 \exp((t-8.1)/4.0)]$$

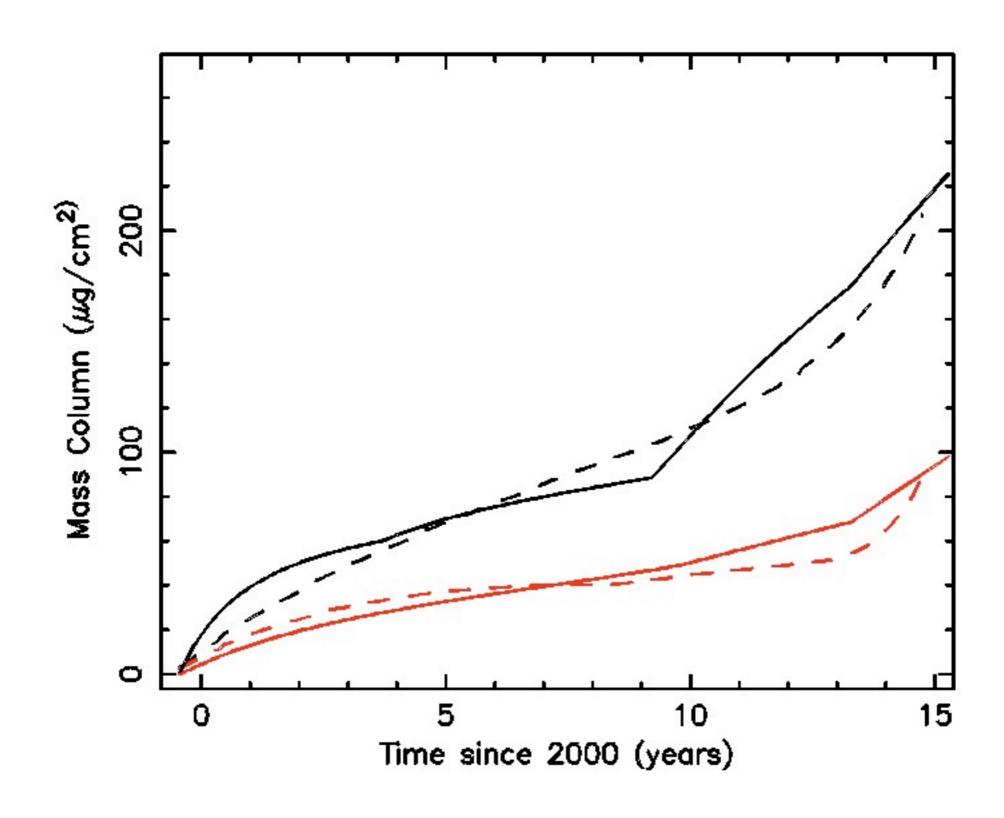


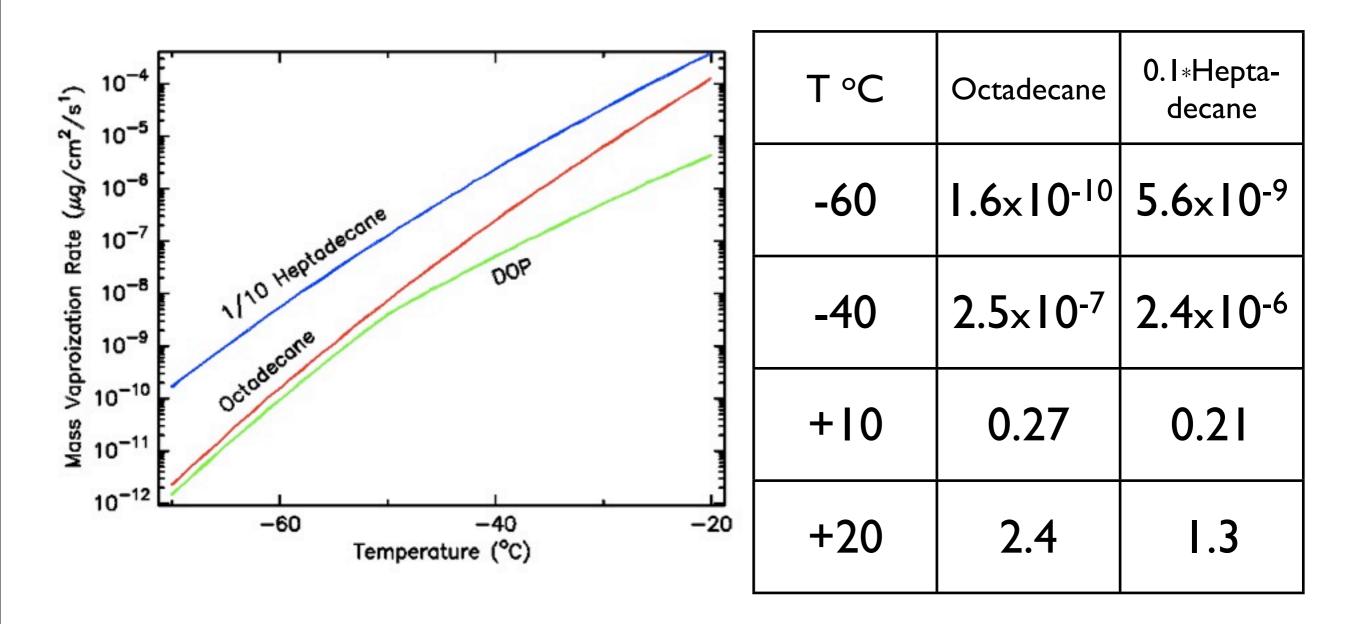
$$S'(t) = S'(T_0) (T_{\text{OBA}}(t)/T_0)^{1/2} * exp[-\Delta H/RT_0(T_0 - T_{\text{OBA}}(t))/T_{\text{OBA}}(t)]$$

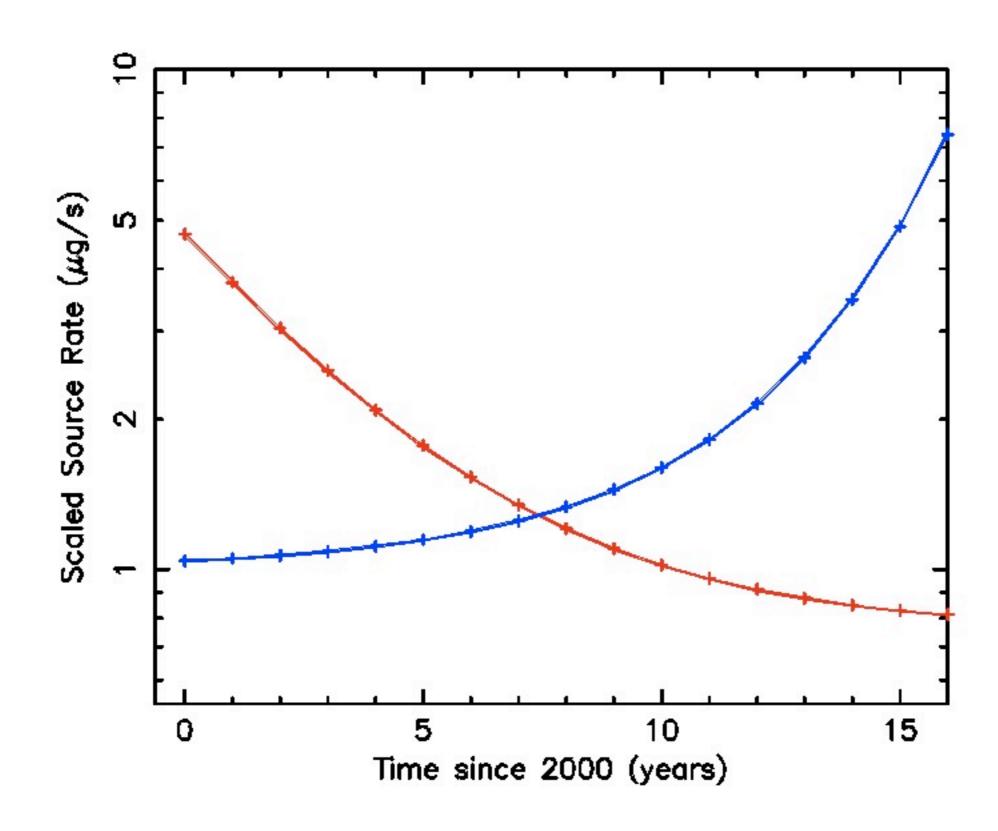
...the Clausius-Clapeyron equation for a time-dependent $T_{\rm OBA}$ (ΔH and T_0 are those of the contaminating material)

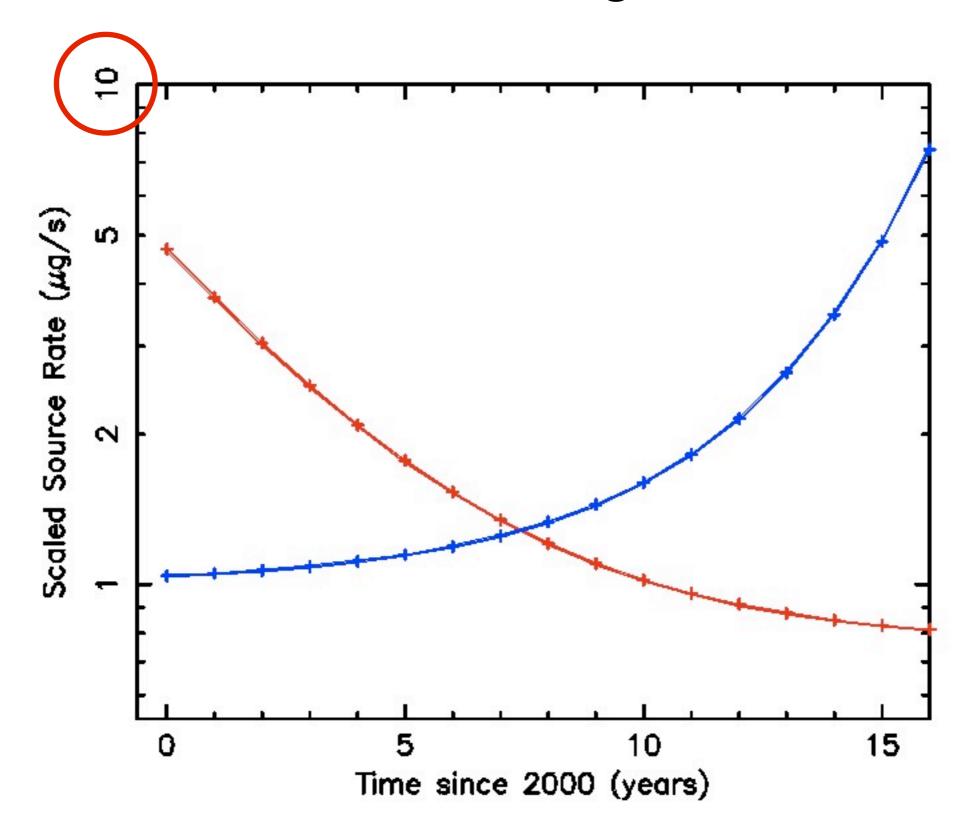


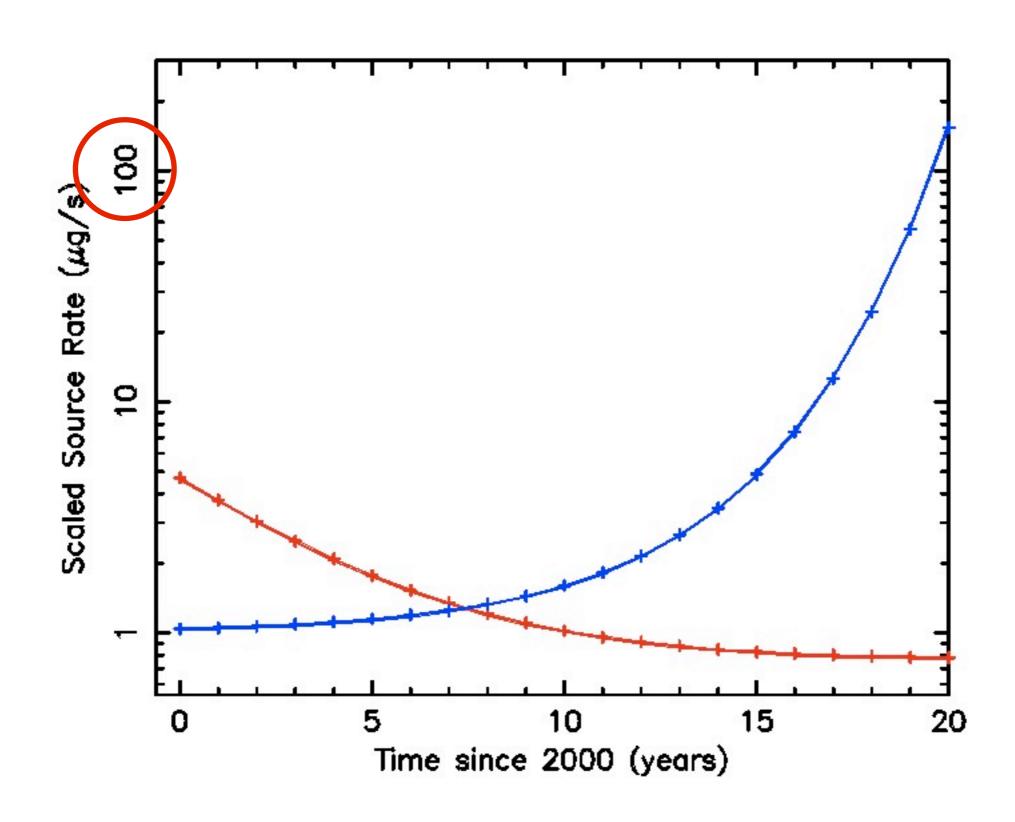






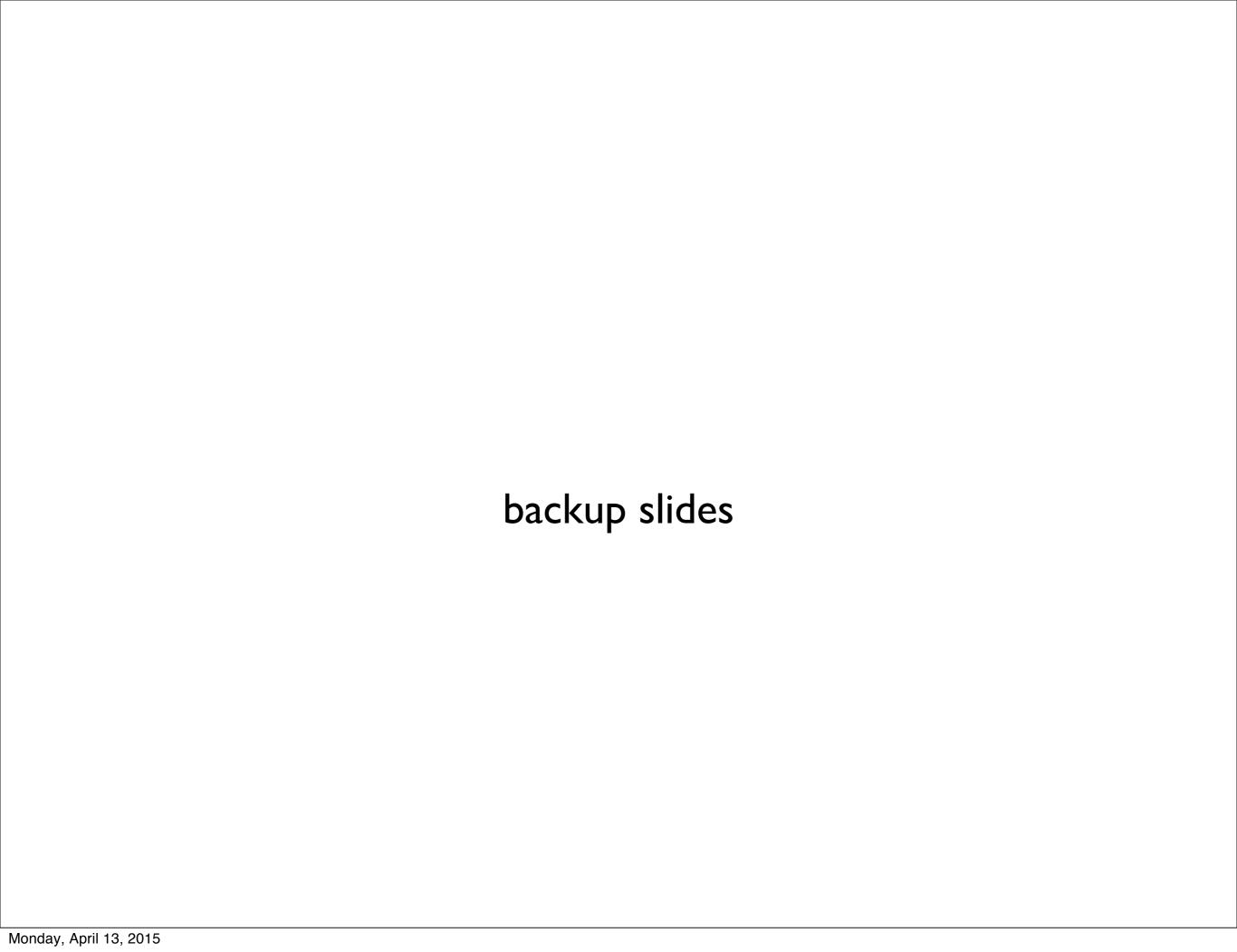


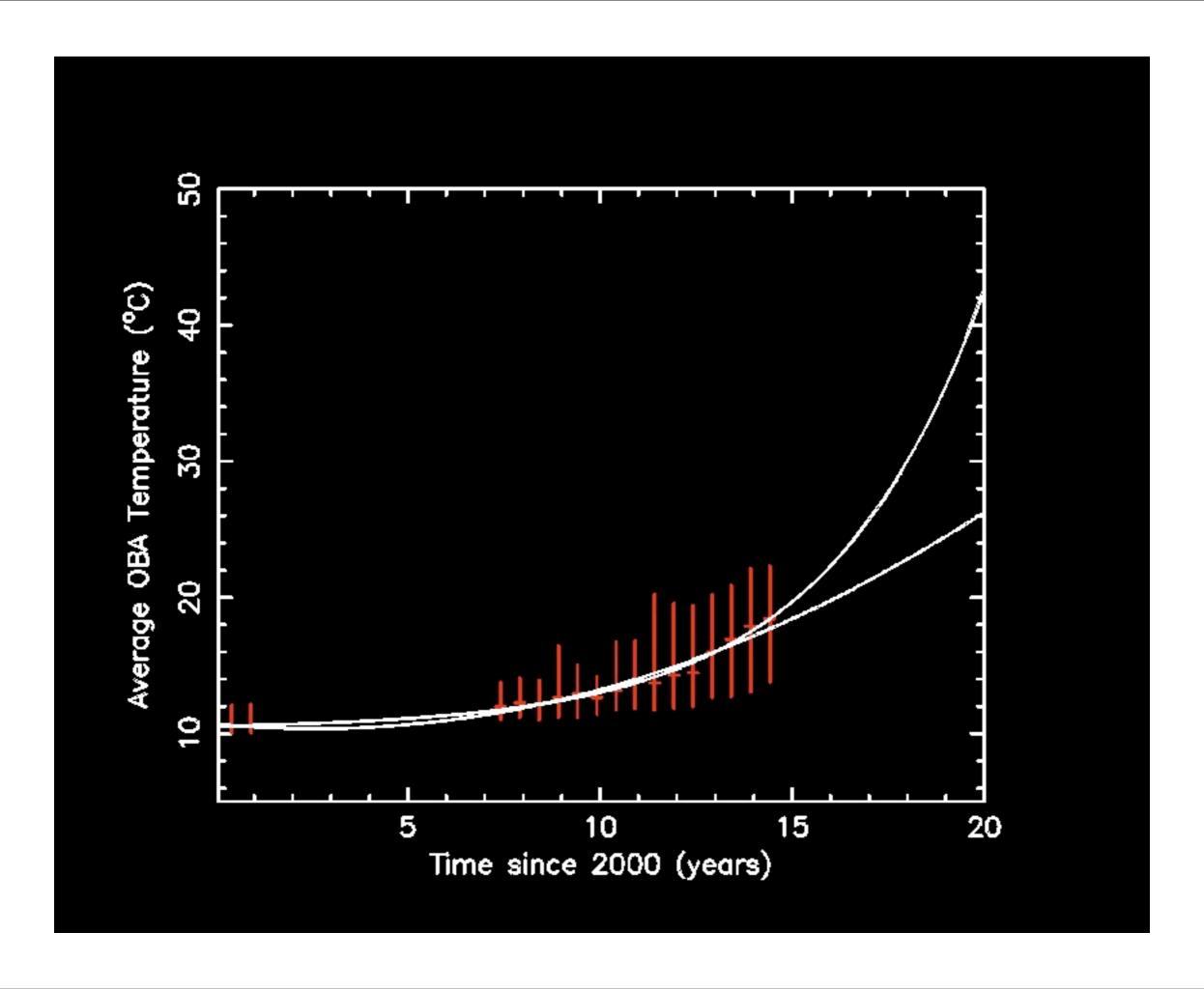




Chandra Contaminant Migration Model SUMMARY

- ◆ Volatility of contaminants can be tightly constrained by simulations.
- ◆ Accelerated buildup since 2010 has 30* higher volatility at -60°C; likely to 'clean' readily at elevated temperatures.
- ◆ Current exponentially increasing trend in OBA temperature is predicted to lead to extremely rapid buildup of 'second' contaminant (5*source rate for 10°C increase in 3 yrs; 30* in 5 yr; but polynomial fit implies only 3* in 5 yr).
- ♦ At t~16 yrs, 0.4 grams of contaminant is within the S/C with only 5% (20mg) on OBFs (~270 μ g/cm²).

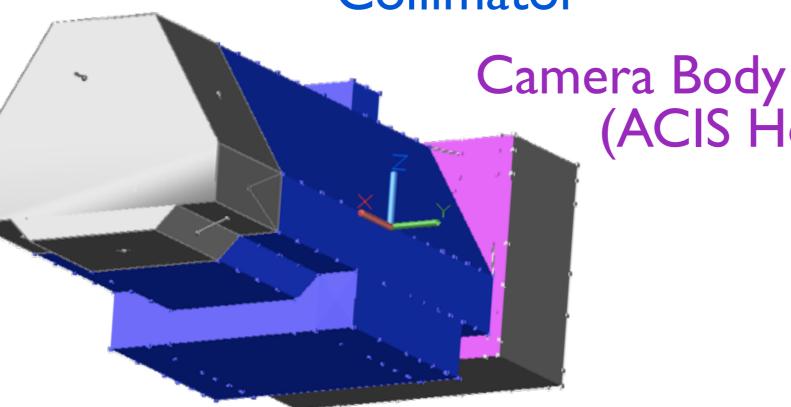




Optical Bench

Geometry Model

Closeout Collimator



From Neil Tice/LMC

Thermal Desktop (finite element): RADCAD

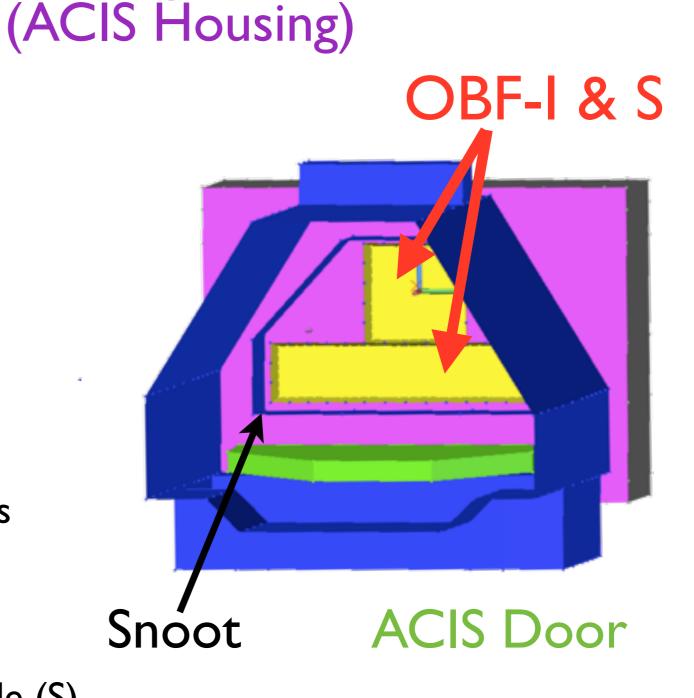
to calculate geometric view factors

SINDA FLUINT

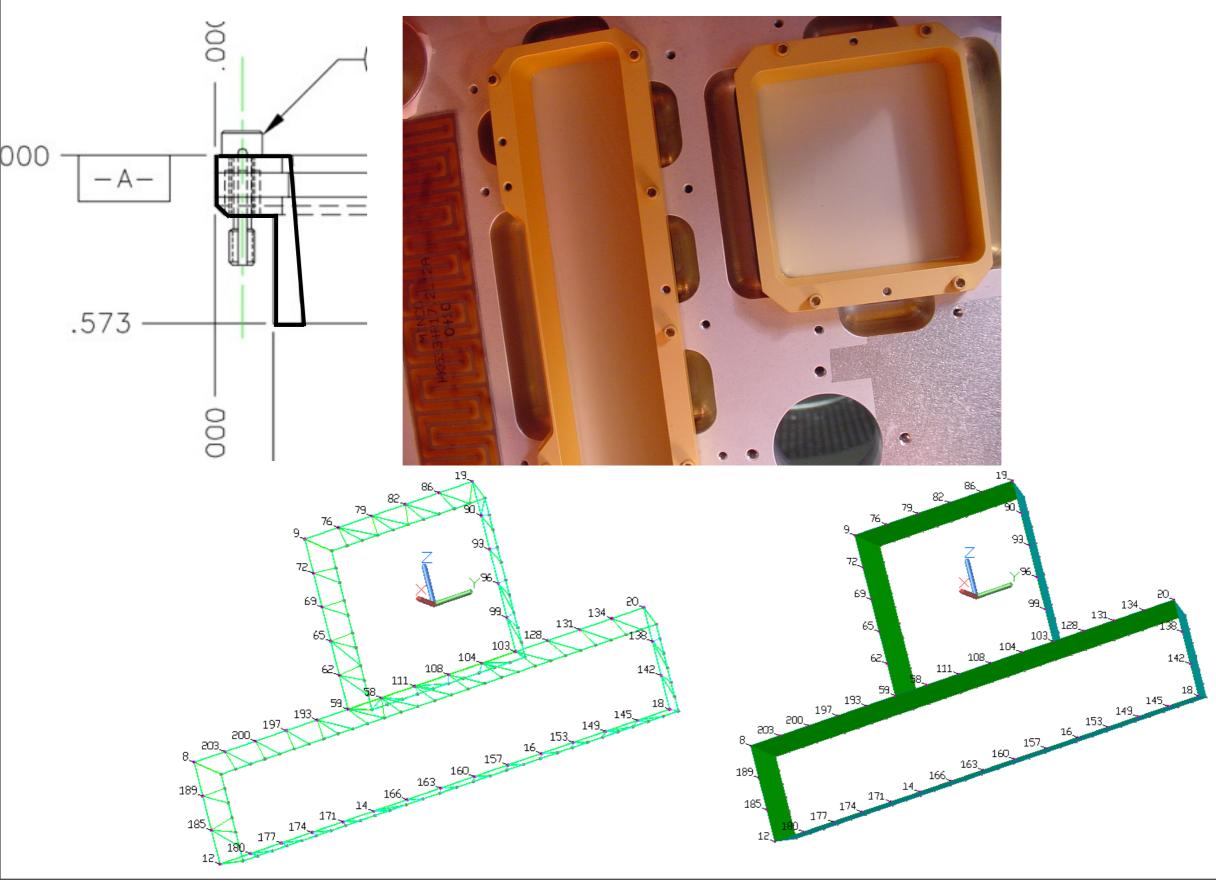
to calculate temperatures

738 nodes, 121 OBF-I, 203 OBF-S

186x186p/node (I), 146x212p/node (S)

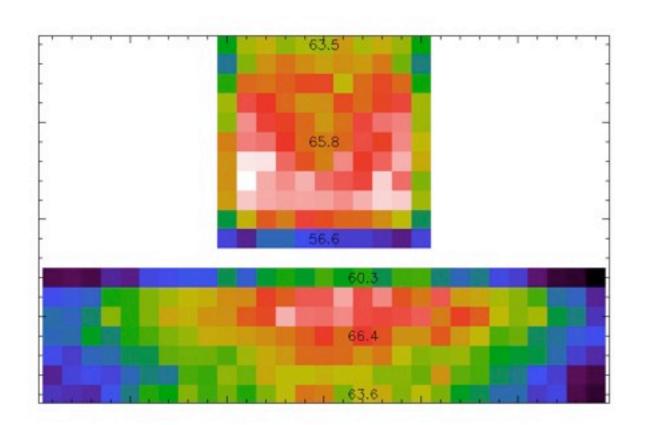


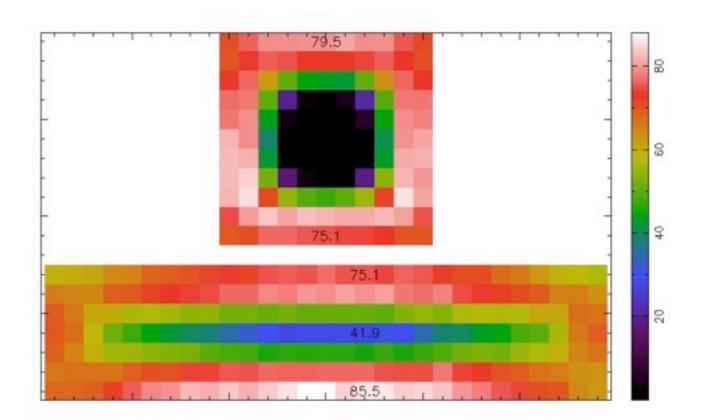
Geometry Model



Chandra Contaminant Migration Model Results

Mass Column of Octadecane ($C_{18}H_{38}$) at t=9 years





low volatility (0.10)

"deposition" dominated: central regions have highest accumulation because center views more nearby cold surfaces, pattern is asymmetric

high volatility (2.50)

"thermal" (vaporization) dominated: warm central regions begin to clean, pattern follows local temperature distribution with more material near cold edges